SQJ411EP

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Vishay Siliconix

Automotive P-Channel 12 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	-12
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.0058
$R_{DS(on)}$ (Ω) at V_{GS} = -2.5 V	0.0087
I _D (A)	-60
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

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RoHS COMPLIANT HALOGEN FREE

Configuration	Sirigie	P-Channel MOSFET				
Package	PowerPAK SO-8L					
ABSOLUTE MAXIMUM	RATINGS (T _C = 25 °C, un	less otherwise noted	d)			
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	-12	V			
Gate-Source Voltage	V _{GS}	± 8	v			
Continuous Drain Current	T _C = 25 °C		-60			
	T _C = 125 °	- I _D	-52			
Continuous Source Current (Diod	e Conduction) ^a	I _S	-60	А		
Pulsed Drain Current ^b		I _{DM}	-110			
Single Pulse Avalanche Current	L = 0.1 m	I _{AS}	-30			
Single Pulse Avalanche Energy	L = 0.1 m	E _{AS}	45	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C		68	w		
	T _C = 125 °	C	22	vv		
Operating Junction and Storage	Temperature Range	T _J , T _{stg}	-55 to +175	°C		
Soldering Recommendations (Pe	ak Temperature) ^{d, e}		260	C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	68	°C/W
Junction-to-Case (Drain)		R _{thJC}	2.2	C/W

Notes

- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. See Solder Profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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a. Package limited.



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SPECIFICATIONS (T _C = 25 °C, u								
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static		-1			T	r		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = -250 μA	-12	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V_{GS} , I_D = -250 μ A	-0.45	-0.6	-1.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	= 0 V, V _{GS} = ± 8 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = -12 V	-	-	-1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = -12 V, T _J = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V _{DS} = -12 V, T _J = 175 °C	-	-	-250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = -4.5 V$	$V_{DS} \le -5 V$	-30	-	-	Α	
		$V_{GS} = -4.5 V$	I _D = -15 A	-	0.0048	0.0058		
Drain-Source On-State Resistance ^a	D	$V_{GS} = -4.5 V$	I _D = -15 A, T _J = 125 °C	-	-	0.0074	Ω	
Drain-Source On-State Resistance *	R _{DS(on)}	$V_{GS} = -4.5 V$	I _D = -15 A, T _J = 175 °C	-	-	0.0082	52	
		$V_{GS} = -2.5 V$	I _D = -10 A	-	0.0072	0.0087	1	
Forward Transconductance b	9 _{fs}	V _{DS} =	-15 V, I _D = -15 A	-	73	-	S	
Dynamic ^b					•			
Input Capacitance	C _{iss}			-	6990	9100		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = -6 V, f = 1 MHz	-	2450	3200	pF	
Reverse Transfer Capacitance	C _{rss}			-	1960	2600		
Total Gate Charge ^c	Qg			-	99	150		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = -4.5 V	$V_{DS} = -6 V, I_D = -1 A$	-	12	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	29	-		
Gate Resistance	Rg		f = 1 MHz	0.5	1.1	1.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	32	50		
Rise Time ^c	t _r	- Vo	$= -6 \text{ V}, \text{ R}_{\text{I}} = 6 \Omega$	-	36	60		
Turn-Off Delay Time ^c	t _{d(off)}	I _D ≅ -1 A, \	$I_{\text{GEN}} = -4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	198	300	ns	
Fall Time ^c	t _f			-	75	115	1	
Source-Drain Diode Ratings and Charac	teristics b				•		1	
Pulsed Current ^a	I _{SM}			-	-	-110	А	
Forward Voltage	V _{SD}	l _F =	= -15 A, V _{GS} = 0	-	-0.8	-1.2	V	
Body diode reverse recovery time	t _{rr}			-	79	160	ns	
Body diode reverse recovery charge	Q _{rr}			-	119	240	nC	
Reverse recovery fall time	ta	I _F = -10	A, di/dt = 100 A/µs	-	37	-		
Reverse recovery rise time	t _b	1		-	47	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			_	-2.7	-6	А	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

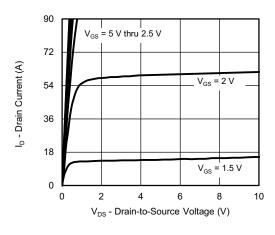
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

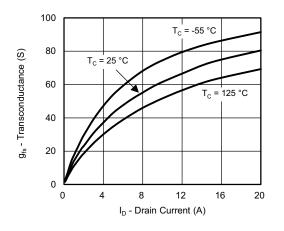
2



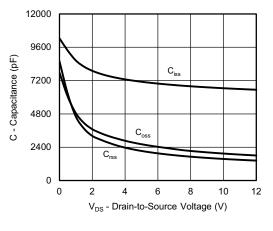
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



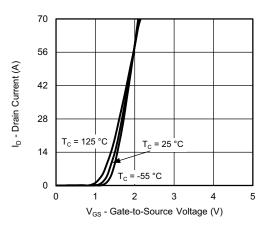
Output Characteristics



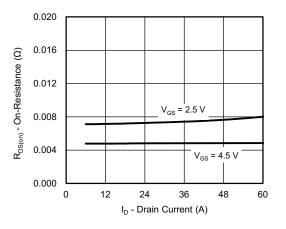
Transconductance



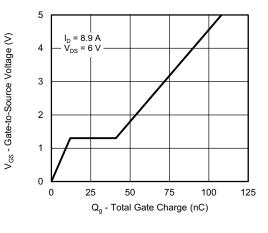
Capacitance







On-Resistance vs. Drain Current



Gate Charge

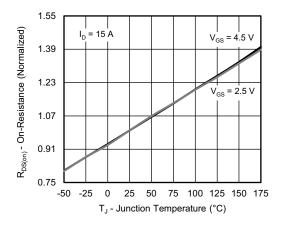
S16-1904-Rev. A, 19-Sep-16

3 stions contact: automostechsupr Document Number: 76549

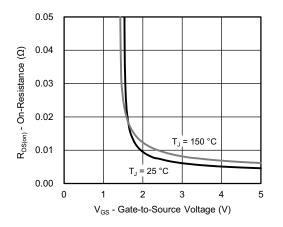
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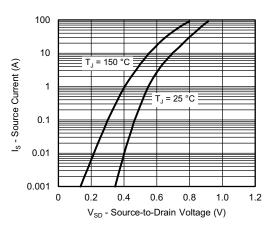
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



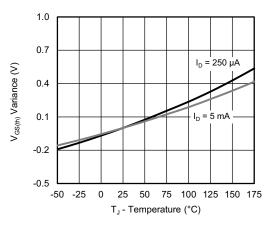
On-Resistance vs. Junction Temperature



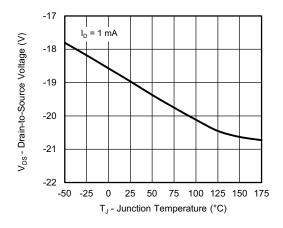
On-Resistance vs. Gate-to-Source Voltage



Source-Drain Diode Forward Voltage



Threshold Voltage

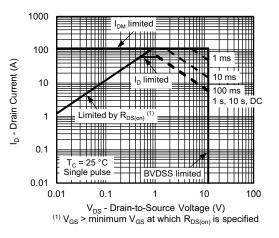


Drain Source Breakdown vs. Junction Temperature

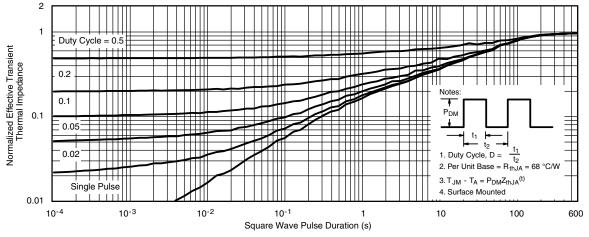
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

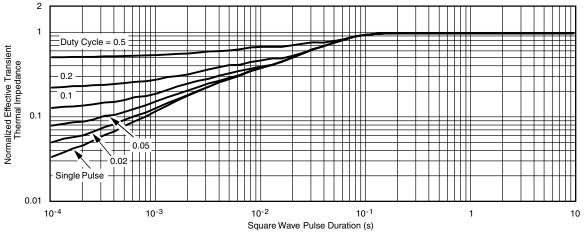


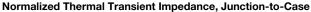
Normalized Thermal Transient Impedance, Junction-to-Ambient



Document Number: 76549

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





Note

• The characteristics shown in the two graphs

S16-1904-Rev. A, 19-Sep-16

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76549.

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Package Information



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DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	MIN. NOM.		
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3	2.96		0.117				
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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